13002AG Preliminary

NPN SILICON TRANSISTOR

HIGH VOLTAGE FAST SWITCHING NPN POWER APPLICATIONS

■ DESCRIPTION

The device is manufactured using High Voltage Multi Epitaxial Planar technology for high switching speeds and high voltage capability.

The UTC **13002AG** is designed for use in Compact Fluorescent Lamps.

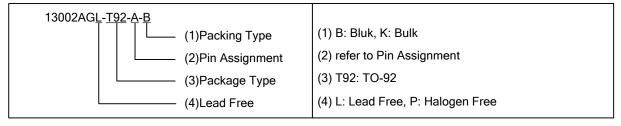
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■ FEATURES

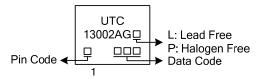
- * High Voltage Capability
- * Low Spread of Dynamic Parameters
- * Very High Switching Speed

■ ORDERING INFORMATION

Ordering Number		Dookago	Pin Assignment			Docking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
13002AGL-T92-A-B	13002AGP-T92-A-B	TO-92	E	С	В	Tape Box	
13002AGL-T92-A-K	13002AGP-T92-A-K	TO-92	Е	С	В	Bulk	



■ MARKING



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■ ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT	
Collector Emitter Voltage (V _{BE} = 0)	V_{CES}	700	V	
Collector Emitter Voltage (I _B = 0)	$V_{\sf CEO}$	400	V	
Emitter Base Voltage (I _C = 0)	V_{EBO}	9	V	
Collector Current	Ic	0.75	Α	
Collector Peak Current (t _p < 5 ms)	I _{CM}	0.5	Α	
Base Current	I_{B}	0.4	Α	
Base Peak Current (t _p < 5 ms)	I _{BM}	0.75	Α	
Total Dissipation at Ta = 25°C	P_D	0.95	W	
Junction Temperature	TJ	+150	°C	
Storage Temperature	T _{STG}	-40 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERAMAL DATA

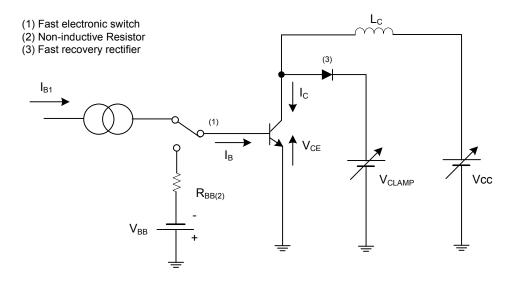
PARAMETER	SYMBOL	RATINGS	UNIT
Thermal Resistance Junction-ambient	θ_{JA}	130	°C /W

■ **ELECTRICAL CHARACTERISTICS** (T_A= 25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Emitter Sustaining Voltage (I _B = 0) (Note)	V _{CEO(SUS)}	I _C = 1 mA	700			V
	V _{CE(SAT)}	$I_C = 0.2 \text{ A}$, $I_B = 40 \text{ mA}$		0.2	0.5	V
Collector Emitter Saturation Voltage (Note)		$I_C = 0.3 \text{ A}$, $I_B = 75 \text{ mA}$		0.3	1	
		I _C = 0.4 A , I _B = 135 mA		0.4	1.5	
Dago Emitter Seturation Voltage (Note)	V _{BE(SAT)}	$I_C = 0.2 \text{ A}$, $I_B = 40 \text{ mA}$			1	V
Base Emitter Saturation Voltage (Note)		$I_C = 0.3 A$, $I_B = 75 mA$			1.2	V
Emitter Cut off Current (I _C = 0)	I _{EBO}	V _{EB} = 9 V			1	mA
Collector Cut off Current (V _{BE} = -1.5V)	I _{CEV}	V _{CE} = 700 V			250	μΑ
DC Current Gain	h _{FE*}	$I_C = 0.2 \text{ A}, V_{CE} = 5 \text{ V}$	12		27	
DC Current Gain		I _C = 0.4 A, V _{CE} = 5 V	7		20	
Inductive Load Fall Time	t _F	I _C = 0.2 A , V _{CLAMP} = 300 V I _{B1} = -I _{B2} = 40 mA , L = 3 mH		0.3		μs

Note: Pulsed: Pulse duration = $300\mu s$, duty cycle = 1.5%

■ INDUCTIVE LOAD SWITCHING TEST CIRCUIT



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